

INFORMATION DISCLOSURE STATEMENT

Applicant	:	To be provided
App. No.	:	Unknown
Filed	:	Herewith
For	:	PROCESS FOR PRODUCING OXIDE FILMS
Examiner	:	Unknown
Group Art Unit	:	Unknown

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing 5 references. Copies of disclosed U.S. patents and/or publications are not included pursuant to PTO waiver of the requirement under 37 C.F.R. § 1.98(a)(2)(i) for applications filed after June 30, 2003. Copies of all other references, if listed, are enclosed.

This Information Disclosure Statement is being filed with an RCE or within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,
KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: October 28, 2003

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. SEPP24.004AUS	APPLICATION NO. Unknown
	APPLICANT To be provided	
	FILING DATE Herewith	GROUP Unknown

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	1	WO 02/27063 A2	04/04/02	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	2	Shin et al., "Plasma-Enhanced Atomic Layer Deposition of SrTa ₂ O ₆ and SrBi ₂ Ta ₂ O ₉ Thin Films"; Atomic Layer Deposition (ALD 2002) Conference, Hanyang University, Seoul Korea, August 19-21, pp. 1-18 (2002)
	3	Williams et al. "Crystal Structure of Bi(OCMe ₂ CH ₂ Ome) ₃ and Its Use in the MOCVD of Bi ₂ O ₃ ***"; Chemical Vapor Deposition; pp. 205-206 (2001)
	4	Gordon et al. "Vapor Deposition of Metal Oxides and Silicates: Possible Gate Insulators for Future Microelectronics"; Chem. Mater.; Vol. 13; pp. 2463-2464 (2001)
	5	Ritala et al. Chapter 2, "Atomic Layer Deposition"; Handbook of Thin Film Materials; Vol. 1: Deposition and Processing of Thin Films; pp. 103-159 (2002)

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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	